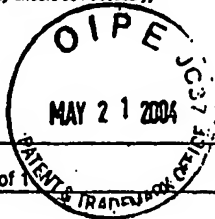


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**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
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Complete if Known	
Application Number	10/721585
Filing Date	November 25, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2825-2891
Examiner Name	Unknown C. Everhart

Sheet 1 of 1

Attorney Docket No: 1303.017US2

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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
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	Application Number	Unknown 10/721,585
	Filing Date	Even Date Herewith 11/25/03
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2625 2891
	Examiner Name	Unknown C. Evenhart
Sheet 1 of 2		Attorney Docket No: 1303.017US2

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown 10/721,555
	Filing Date	Even Date Herewith 11/25/03
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2826 2891
	Examiner Name	Unknown C. Everhart
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